



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	2Ω @ $V_{GS} = 10V$	380mA
60 V	3Ω @ V _{GS} = 5V	310mA

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{\rm DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The 2N7002KQ is suitable for automotive applications requiring specific change control; it is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.
- https://www.diodes.com/quality/product-definitions/

Mechanical Data

Case: SOT23

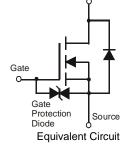
Drain

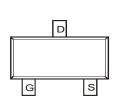
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)





Top View





Top View

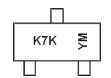
Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
2N7002K-7	Standard	SOT23	3000/Tape & Reel
2N7002KQ-7	Automotive	SOT23	3000/Tape & Reel
2N7002K-13	Standard	SOT23	10000/Tape & Reel
2N7002KQ-13	Automotive	SOT23	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $K7K = Product Type Marking Code YM or <math>\overline{Y}M = Date Code Marking Y or \overline{Y} = Year (ex: F = 2018) M = Month (ex: 9 = September)$

Date Code Kev

Year	2006	~	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027
Code	Т	٠	F	G	Н	I	J	K	L	М	N	0
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

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October 2019
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Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Dusin Comment (Alata C) V 40V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	380 300	mA
Continuous Drain Current (Note 6) V _{GS} = 10V	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	430 340	mA
Continuous Dusin Comment (Alata C) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	310 240	mA
Continuous Drain Current (Note 6) V _{GS} = 5V	t<5s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	350 270	mA
Maximum Continuous Body Diode Forward Current (Note 6)			Is	0.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	6) (Note 6))	I _{DM}	1.2	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)		P_{D}	370	mW	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	5	357	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	292	C/VV	
Total Power Dissipation (Note 6)		P_{D}	540	mW	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	5	240		
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	197	°C/W	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	91		
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

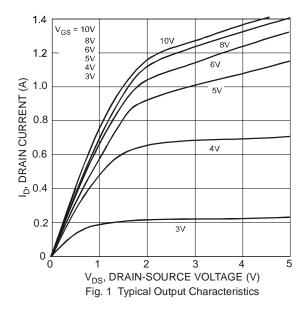
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$
Static Drain-Source On-Resistance	р		_	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	3.0	12	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	V_{SD}	_	0.75	1.1	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	30	50	pF	V 05V V 0V
Output Capacitance	C _{oss}	_	4.2	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_	2.9	5.0	pF	1 = 1.0lviH2
Gate Resistance	R_{g}	_	133	_	Ω	$f = 1MHz$, $V_{GS} = 0V$, $V_{DS} = 0V$
Total Gate Charge	Q_{g}	_	0.3	_	nC	V 45V V 40V
Gate-Source Charge	Q _{gs}	_	0.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q_{gd}	_	0.08	_	nC	I _D = 250mA
Turn-On Delay Time	t _{D(ON)}	_	3.9	_	ns	
Turn-On Rise Time	t _R	_	3.4	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$
Turn-Off Delay Time	t _{D(OFF)}	_	15.7	_	ns	$R_G = 25\Omega$, $I_D = 200mA$
Turn-Off Fall Time	t _F	_	9.9		ns	

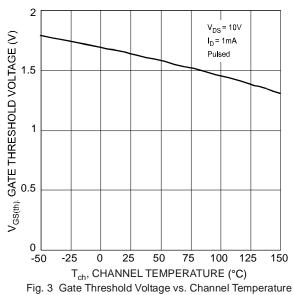
5. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

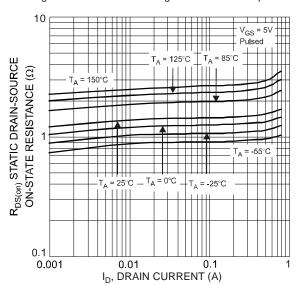
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.

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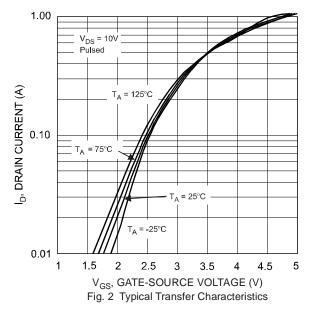












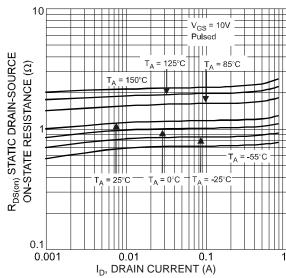


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

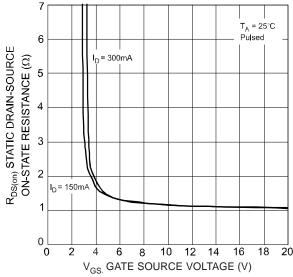


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



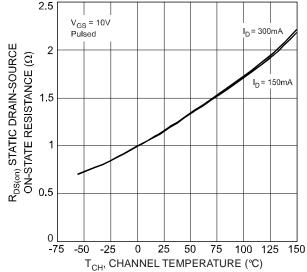


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

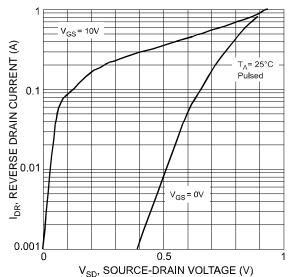
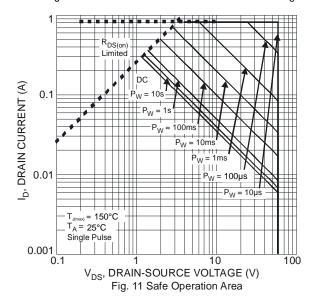
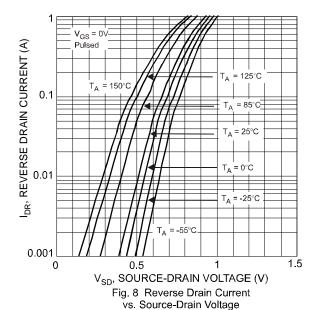


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage





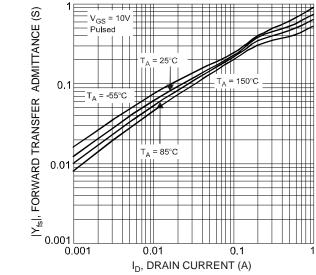
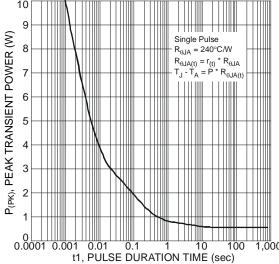
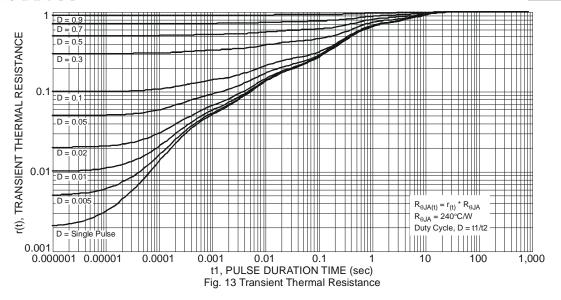


Fig. 10 Forward Transfer Admittance vs. Drain Current

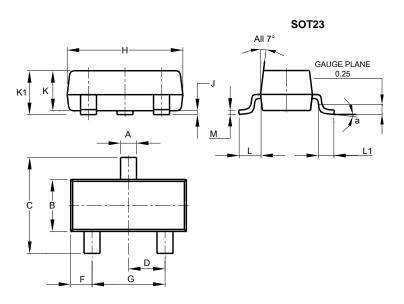






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

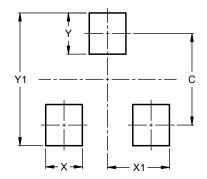


SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All	All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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